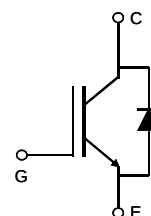
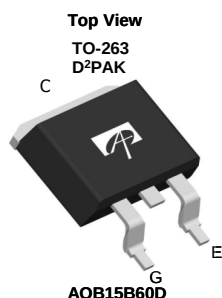


General Description

The Alpha IGBT™ line of products offers best-in-class performance in conduction and switching losses, with robust short circuit capability. They are designed for ease of paralleling, minimal gate spike under high dV/dt conditions and resistance to oscillations. The soft co-package diode is targeted for minimal losses in motor control applications.

Product Summary

V_{CE}	600V
I_C ($T_C=100^\circ\text{C}$)	15A
$V_{CE(sat)}$ ($T_C=25^\circ\text{C}$)	1.6V



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	AOB15B60D	Units
Collector-Emitter Voltage	V_{CE}	600	V
Gate-Emitter Voltage	V_{GE}	± 20	V
Continuous Collector Current	I_C	$T_C=25^\circ\text{C}$	A
		$T_C=100^\circ\text{C}$	
Pulsed Collector Current, Limited by T_{Jmax}	I_{CM}	60	A
Turn off SOA, $V_{CE} \leq 600\text{V}$, Limited by T_{Jmax}	I_{LM}	60	A
Continuous Diode Forward Current	I_F	$T_C=25^\circ\text{C}$	A
		$T_C=100^\circ\text{C}$	
Diode Pulsed Current, Limited by T_{Jmax}	I_{FM}	60	A
Short circuit withstanding time $V_{GE} = 15\text{V}$, $V_{CE} \leq 400\text{V}$, Delay between short circuits $\geq 1.0\text{s}$, $T_C=150^\circ\text{C}$	t_{SC}	10	μs
Power Dissipation	P_D	$T_C=25^\circ\text{C}$	W
		$T_C=100^\circ\text{C}$	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	T_L	300	$^\circ\text{C}$

Thermal Characteristics

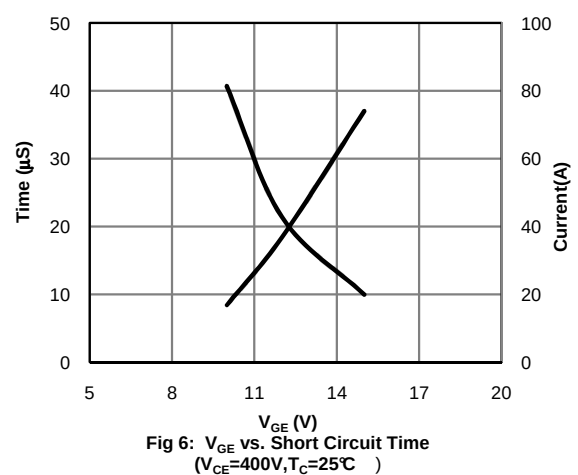
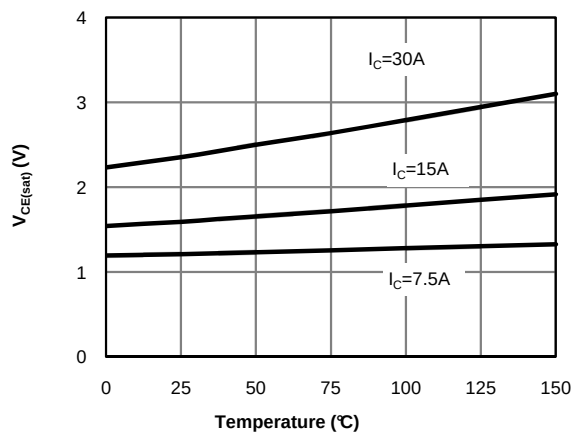
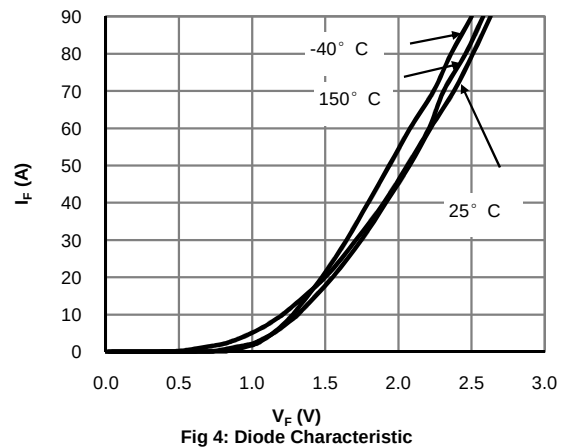
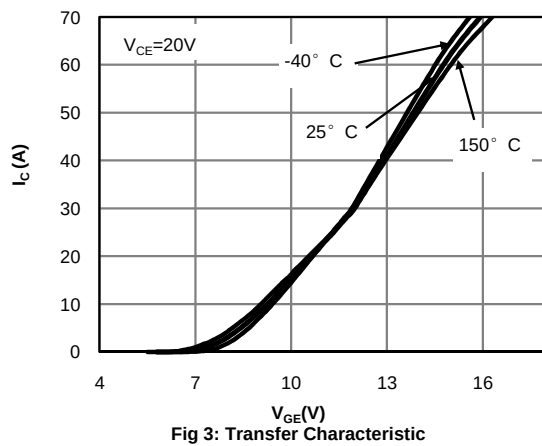
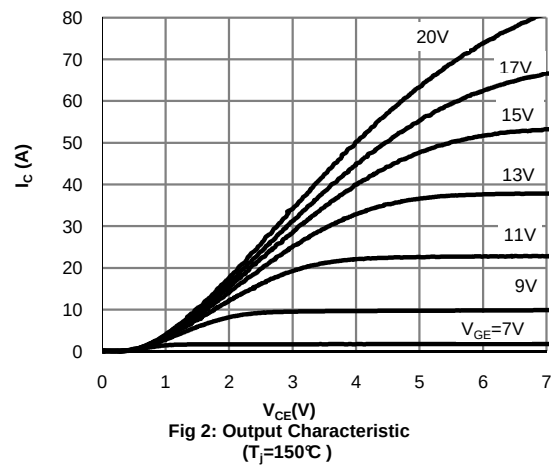
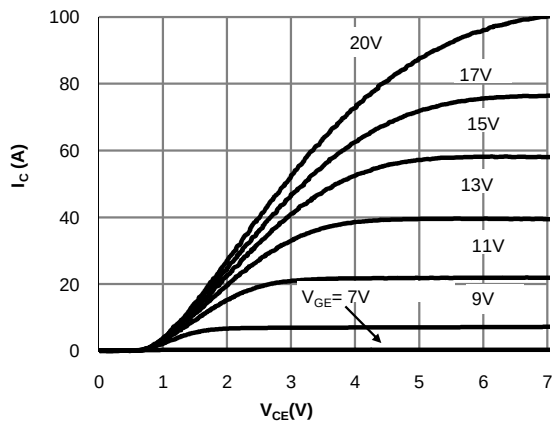
Parameter	Symbol	AOB15B60D	Units
Maximum Junction-to-Ambient	$R_{\theta JA}$	65	$^\circ\text{C/W}$
Maximum IGBT Junction-to-Case	$R_{\theta JC}$	0.9	$^\circ\text{C/W}$
Maximum Diode Junction-to-Case	$R_{\theta JC}$	1.5	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

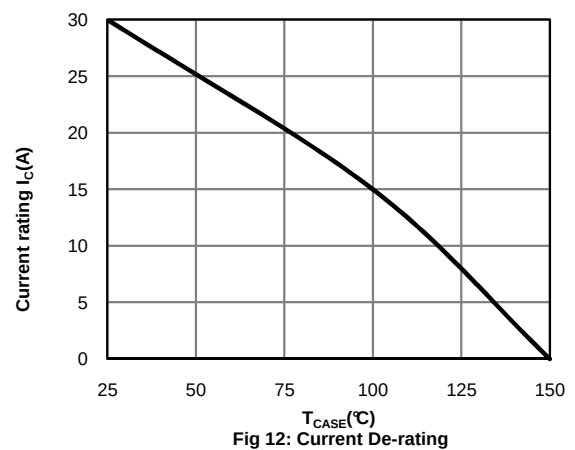
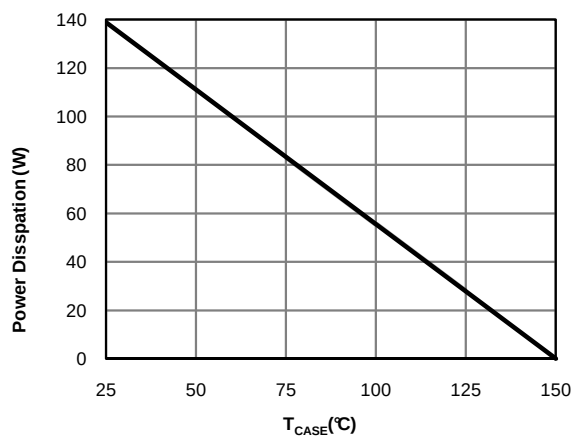
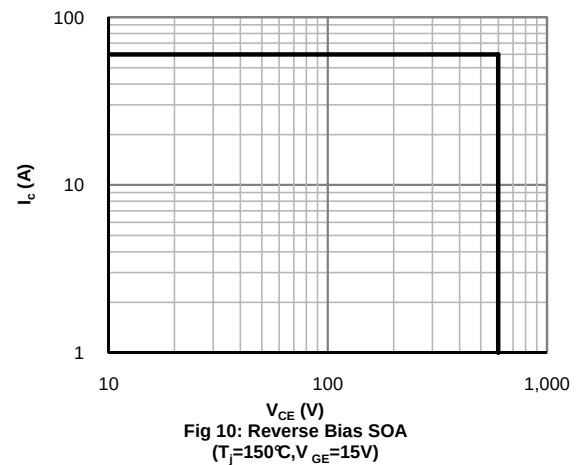
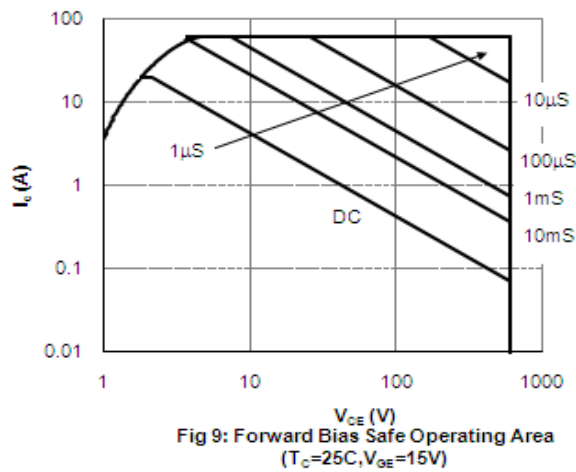
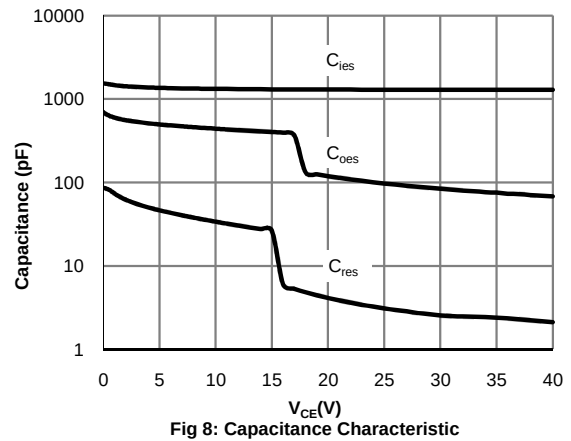
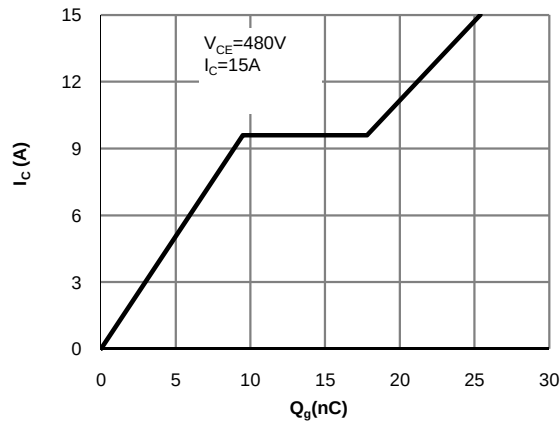
Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{CES}	Collector-Emitter Breakdown Voltage	$I_C=1mA, V_{GE}=0V, T_J=25^{\circ}C$	600	-	-	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15V, I_C=15A$	$T_J=25^{\circ}C$	-	1.6	1.8
			$T_J=125^{\circ}C$	-	1.85	-
			$T_J=150^{\circ}C$	-	1.92	-
V_F	Diode Forward Voltage	$V_{GE}=0V, I_C=15A$	$T_J=25^{\circ}C$	-	1.43	1.72
			$T_J=125^{\circ}C$	-	1.39	-
			$T_J=150^{\circ}C$	-	1.36	-
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=1mA$	-	5.8	-	V
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE}=600V, V_{GE}=0V$	$T_J=25^{\circ}C$	-	-	10
			$T_J=125^{\circ}C$	-	-	300
			$T_J=150^{\circ}C$	-	-	1500
I_{GES}	Gate-Emitter leakage current	$V_{CE}=0V, V_{GE}=\pm 20V$	-	-	± 100	nA
g_{FS}	Forward Transconductance	$V_{CE}=20V, I_C=15A$	-	7.7	-	S
DYNAMIC PARAMETERS						
C_{ies}	Input Capacitance	$V_{GE}=0V, V_{CE}=25V, f=1MHz$	-	1290	-	pF
C_{oes}	Output Capacitance		-	97	-	pF
C_{res}	Reverse Transfer Capacitance		-	3.1	-	pF
Q_g	Total Gate Charge	$V_{GE}=15V, V_{CE}=480V, I_C=15A$	-	25.4	-	nC
Q_{ge}	Gate to Emitter Charge		-	9.5	-	nC
Q_{gc}	Gate to Collector Charge		-	8.3	-	nC
$I_{C(SC)}$	Short circuit collector current, Max. 1000 short circuits, Delay between short circuits $\geq 1.0s$	$V_{GE}=15V, V_{CE}=400V, R_G=20\Omega$	-	74	-	A
R_g	Gate resistance	$V_{GE}=0V, V_{CE}=0V, f=1MHz$	-	2.4	-	Ω
SWITCHING PARAMETERS, (Load Inductive, $T_J=25^{\circ}C$)						
$t_{D(on)}$	Turn-On DelayTime	$T_J=25^{\circ}C$ $V_{GE}=15V, V_{CE}=400V, I_C=15A,$ $R_G=20\Omega,$ Parasitic Inductance=100nH	-	21	-	ns
t_r	Turn-On Rise Time		-	19	-	ns
$t_{D(off)}$	Turn-Off Delay Time		-	73	-	ns
t_f	Turn-Off Fall Time		-	10	-	ns
E_{on}	Turn-On Energy		-	0.42	-	mJ
E_{off}	Turn-Off Energy		-	0.11	-	mJ
E_{total}	Total Switching Energy		-	0.53	-	mJ
t_{rr}	Diode Reverse Recovery Time		$T_J=25^{\circ}C$	-	196	-
Q_{rr}	Diode Reverse Recovery Charge	$I_F=15A, dI/dt=200A/\mu s, V_{CE}=400V$	-	0.48	-	μC
I_{rm}	Diode Peak Reverse Recovery Current		-	5.8	-	A
SWITCHING PARAMETERS, (Load Inductive, $T_J=150^{\circ}C$)						
$t_{D(on)}$	Turn-On DelayTime	$T_J=150^{\circ}C$ $V_{GE}=15V, V_{CE}=400V, I_C=15A,$ $R_G=20\Omega,$ Parasitic Inductance=100nH	-	21	-	ns
t_r	Turn-On Rise Time		-	19	-	ns
$t_{D(off)}$	Turn-Off Delay Time		-	91	-	ns
t_f	Turn-Off Fall Time		-	8	-	ns
E_{on}	Turn-On Energy		-	0.54	-	mJ
E_{off}	Turn-Off Energy		-	0.19	-	mJ
E_{total}	Total Switching Energy		-	0.73	-	mJ
t_{rr}	Diode Reverse Recovery Time		$T_J=150^{\circ}C$	-	235	-
Q_{rr}	Diode Reverse Recovery Charge	$I_F=15A, dI/dt=200A/\mu s, V_{CE}=400V$	-	1.1	-	μC
I_{rm}	Diode Peak Reverse Recovery Current		-	8.5	-	A

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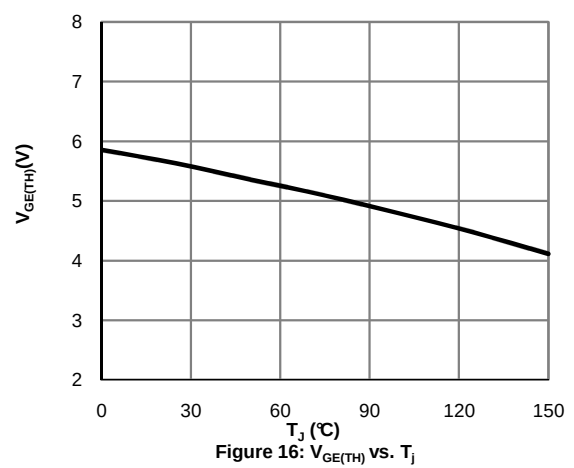
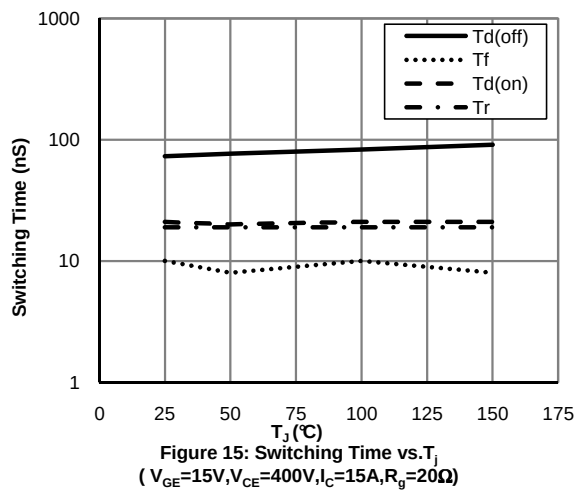
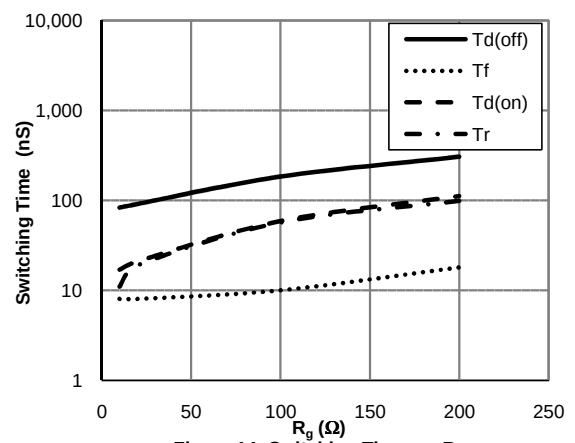
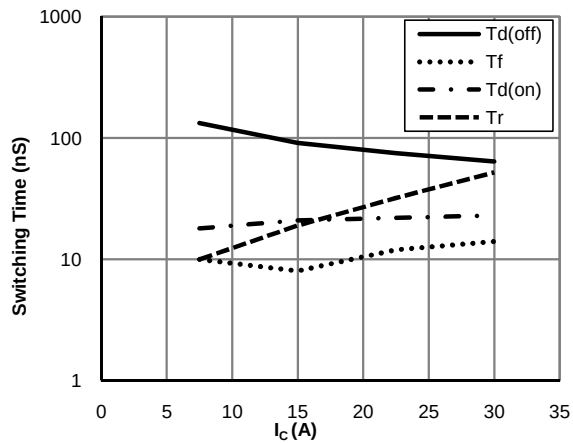
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



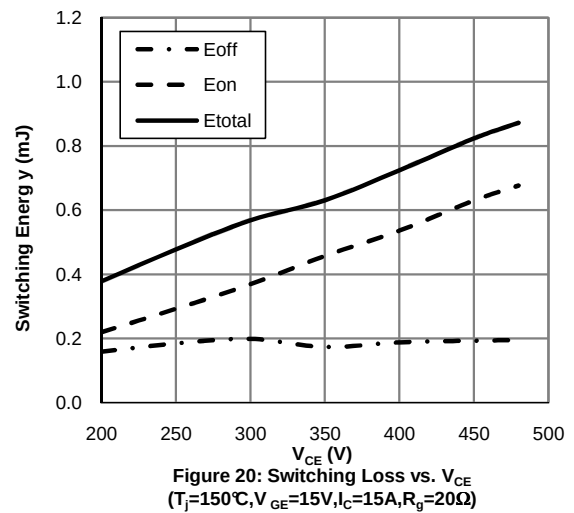
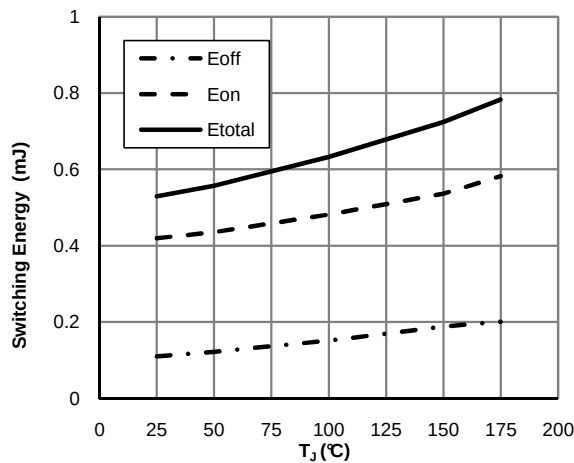
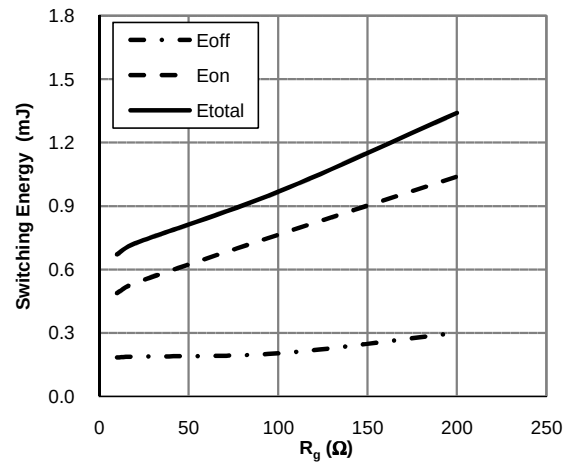
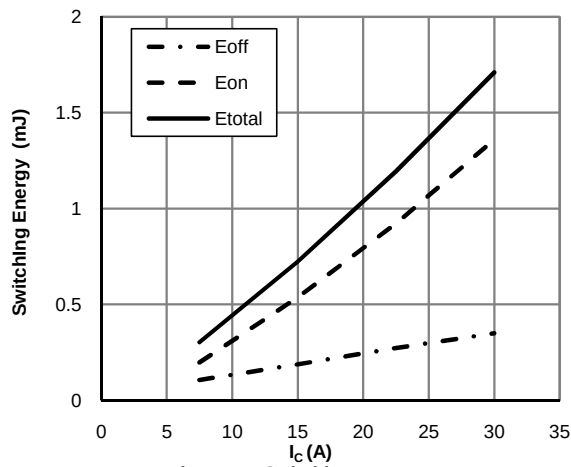
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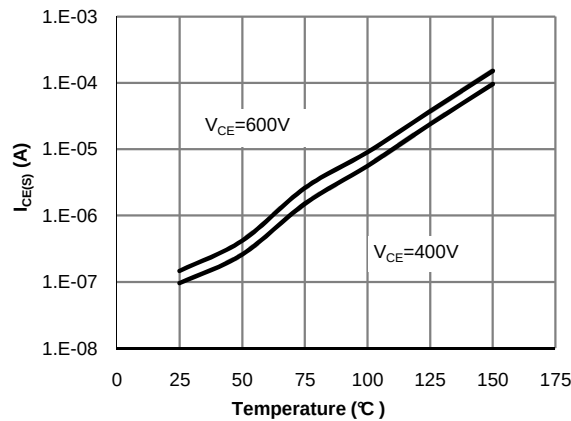


Fig 21: Diode Reverse Leakage Current vs. Junction Temperature

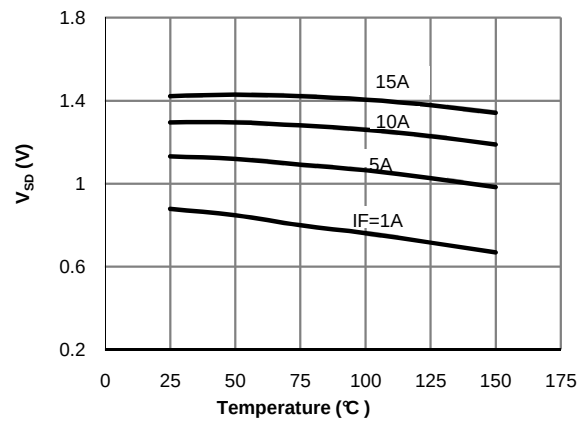


Fig 22: Diode Forward Voltage vs. Junction Temperature

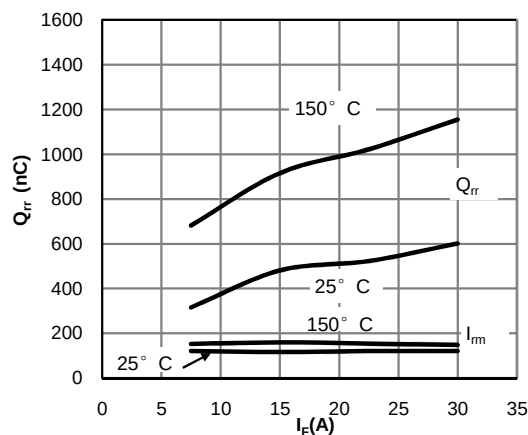


Fig 23: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

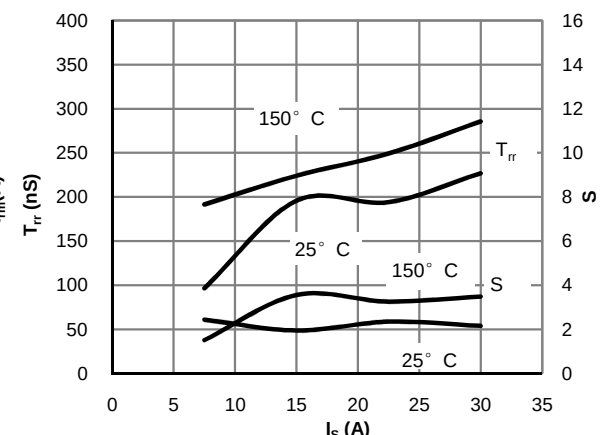


Fig 24: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

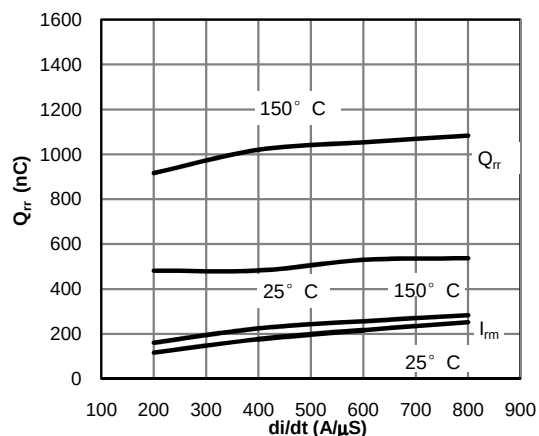


Fig 25: Diode Reverse Recovery Charge and Peak Current vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=15A$)

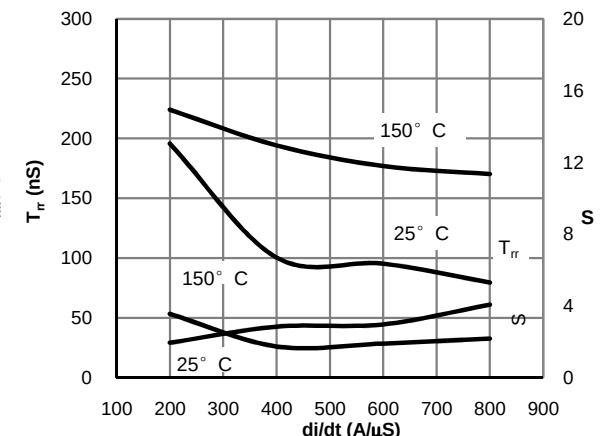


Fig 26: Diode Reverse Recovery Time and Softness Factor vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=15A$)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

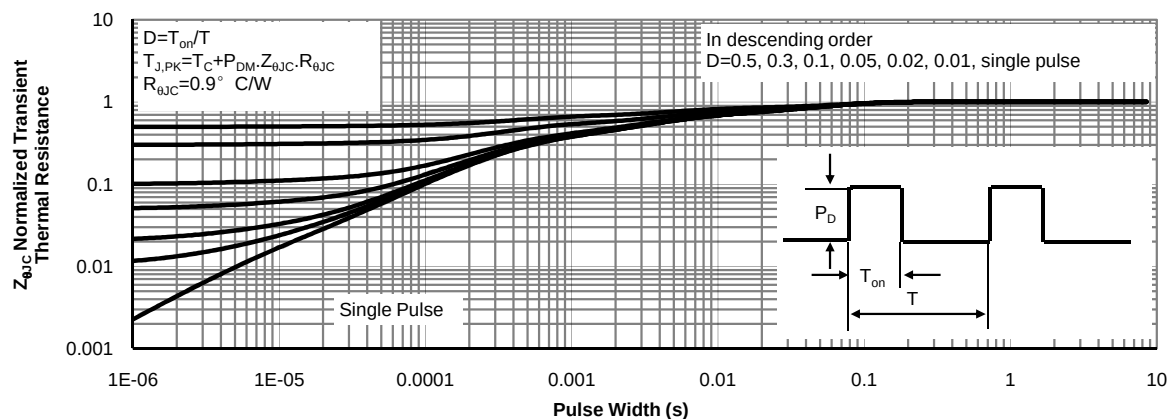


Figure 27: Normalized Maximum Transient Thermal Impedance for IGBT

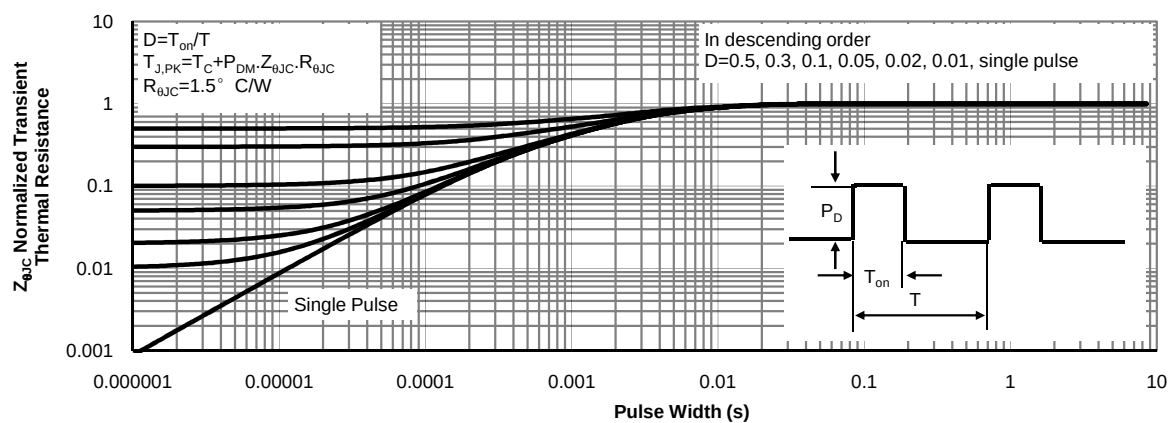
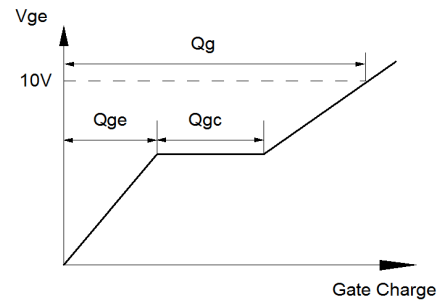
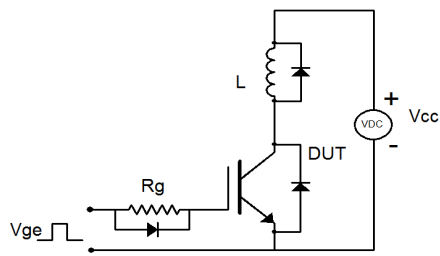
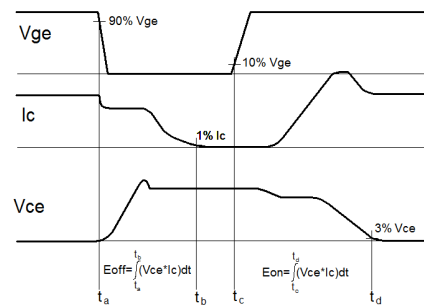
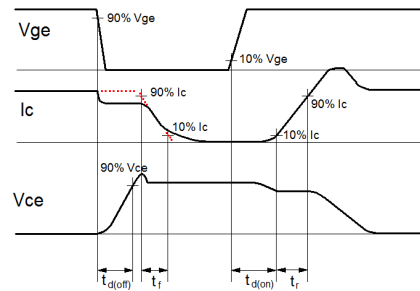
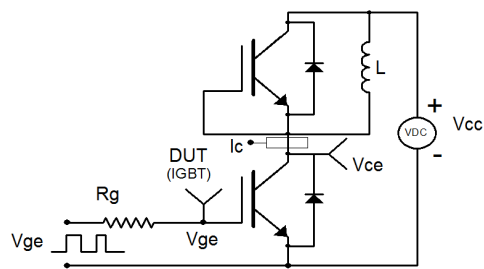


Figure 28: Normalized Maximum Transient Thermal Impedance for Diode

Gate Charge Test Circuit & Waveform



Inductive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

